NCE25G135P

1350V, 25A, Trench NPT IGBT

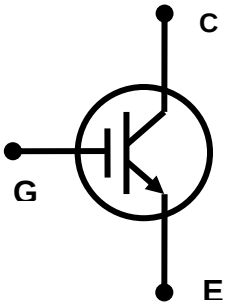


Features

- Trench NPT(Non Punch Through) IGBT
- High speed switching
- Low saturation voltage: $V_{CE(sat)}$=2.0V@I_C=25A
- High input impedance

Applications

- Inductive heating, Microwave oven, Inverter, UPS, etc.
- Soft switching applications



General Description

Using advanced Trench NPT technology, NCE's 1350V IGBTs offers superior conduction and switching performances, and easy parallel operation with exceptional avalanche ruggedness. This device is designed for soft switching applications.

Absolute Maximum Ratings

Symbol	Description	Ratings	Units
V_{CES}	Collector to Emitter Voltage	1350	V
V_{GES}	Gate to Emitter Voltage	+/-30	V
I_C	Continuous Collector Current @T_C=25°C	50	A
	Continuous Collector Current @T_C=100°C	25	A
I_{CM}(1)	Pulsed Collector Current	90	A
P_D	Maximum Power Dissipation @T_C=25°C	312	W
	Maximum Power Dissipation @T_C=100°C	125	W
T_J	Operating Junction Temperature	-55 to +150	°C
T_{stg}	Storage Temperature Range	-55 to +150	°C
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5seconds	300	°C

Notes:

1. Repetitive rating, Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	-	0.4	°C/W
R_{JA}	Thermal Resistance, Junction to Ambient	-	40	°C/W

Electrical Characteristics of the IGBT T_C=25°C

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{CES}	Collector to Emitter Breakdown Voltage	V_{GE}=0V, Ic=1mA	1350	-	-	V
I_{CES}	Collector Cut-Off Current	V_{CE}=1350V, V_{GE}=0V	-	-	1	mA
I_{GES}	G-E Leakage Current	V_{GE}=20V, V_{CE}=0V	-	-	+/-250	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	I_C=25mA, V_{CE}=V_{GE}	4.0	5.5	7.0	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C=25A, V_{GE}=15V T_C=25°C	-	2	2.5	V
		I_C=25A, V_{GE}=15V T_C=125°C	-	2.15	-	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	V_{CE}=30V, V_{GE}=0V, f=1MHz	-	3700	-	pF
C_{oes}	Output Capacitance		-	130	-	pF
C_{res}	Reverse Transfer Capacitance		-	80	-	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=25A, R_G=10Ω,V_{GE}=15V, Resistive Load, T_C=25°C	-	50	-	ns
t_r	Rise Time		-	60	90	ns
$t_{d(off)}$	Turn-Off Delay Time		-	190	-	ns
t_f	Fall Time		-	100	180	ns
E_{on}	Turn-On Switching Loss		-	4.1	6.2	mJ
E_{off}	Turn-Off Switching Loss		-	0.96	1.5	mJ
E_{ts}	Total Switching Loss		-	5.06	7.7	mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=25A, R_G=10Ω,V_{GE}=15V, Resistive Load, T_C=125°C	-	50	-	ns
t_r	Rise Time		-	60	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	200	-	ns
t_f	Fall Time		-	154	-	ns
E_{on}	Turn-On Switching Loss		-	4.3	6.9	mJ
E_{off}	Turn-Off Switching Loss		-	1.5	2.4	mJ
E_{ts}	Total Switching Loss		-	5.8	9.3	mJ
Q_g	Total Gate Charge	V_{CC}=600V,I_C=25A, V_{GE}=15V	-	200	300	nC
Q_{ge}	Gate to Emitter Charge		-	15	23	nC
Q_{gc}	Gate to Collector Charge		-	100	150	nC

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

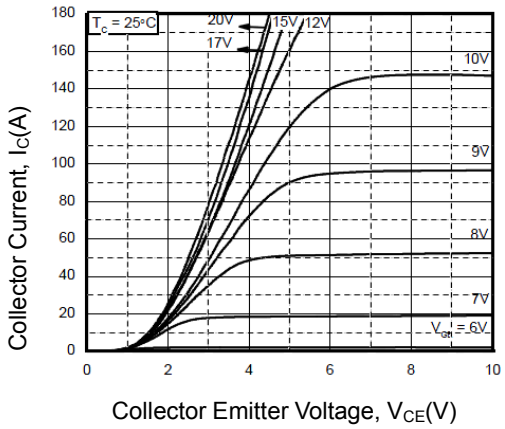


Figure 2. Typical Saturation Voltage Characteristics

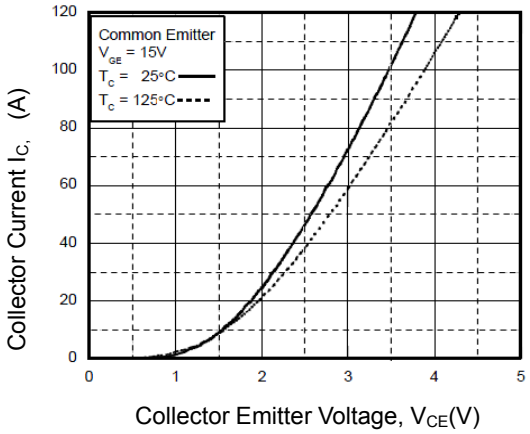


Figure 3. Saturation Voltage vs. Case Temperature at Variant Current Level

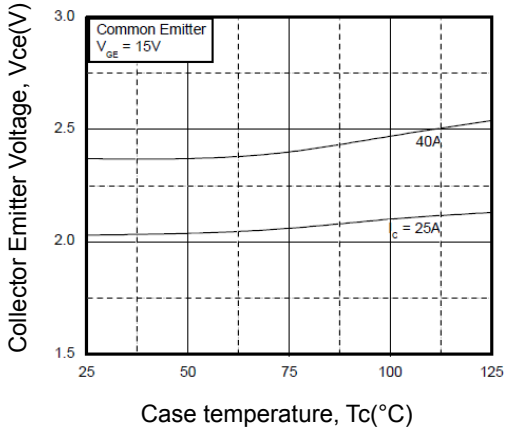


Figure 4. Saturation Voltage vs. V_{GE}

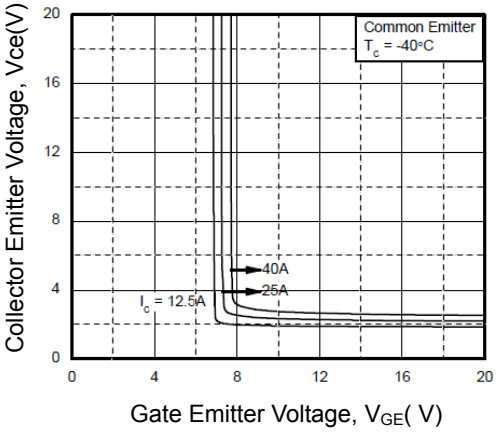


Figure 5. Saturation Voltage vs. V_{GE}

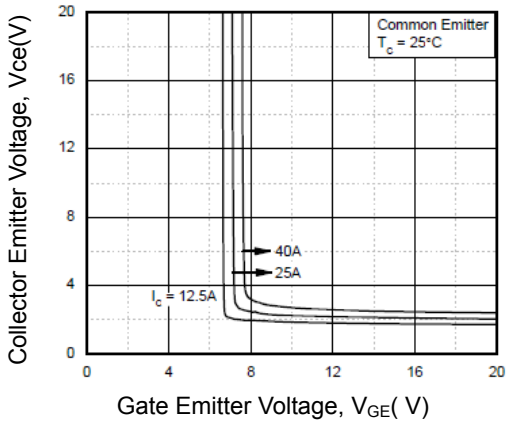
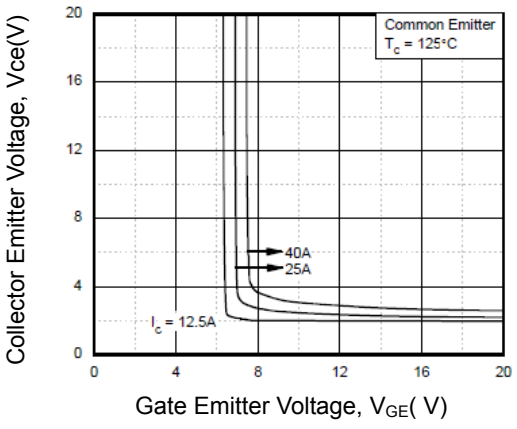


Figure 6. Saturation Voltage vs. V_{GE}



Typical Performance Characteristics (Continued)

Figure 7. Capacitance Characteristics

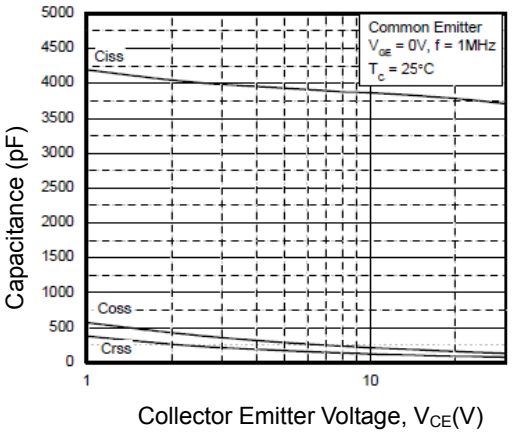


Figure 8. Turn-on Characteristics vs. Gate Resistance

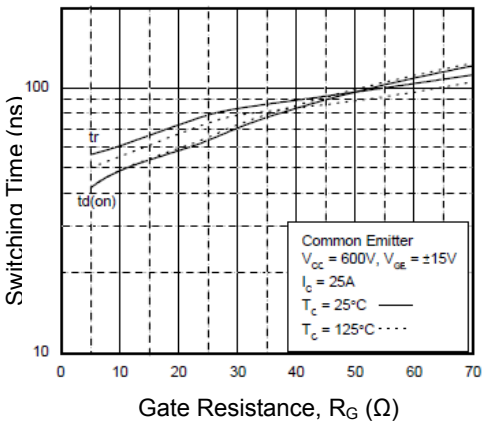


Figure 9. Turn-off Characteristics vs. Gate Resistance

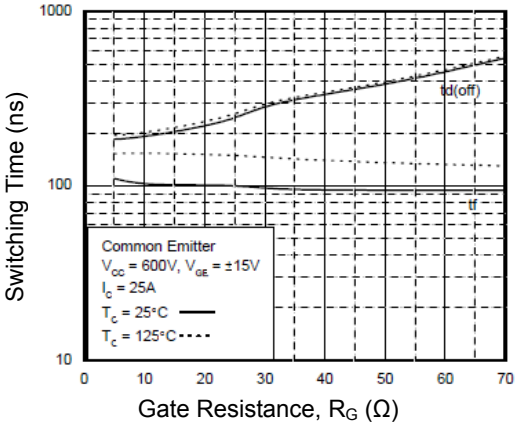


Figure 10. Switching Loss vs. Gate Resistance

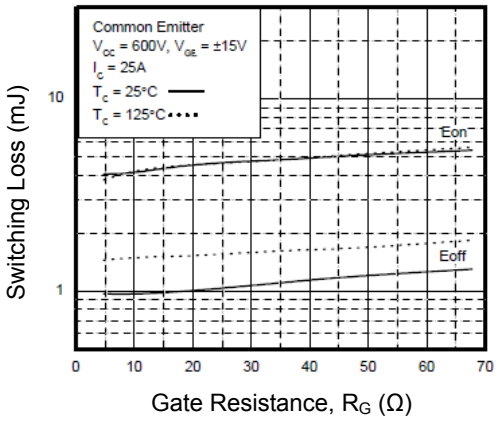


Figure 11. Turn-on Characteristics vs. Collector Current

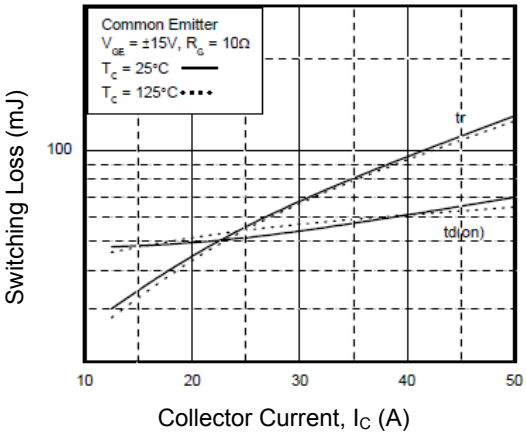
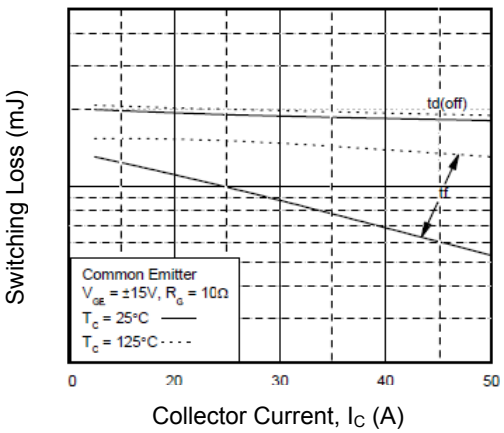


Figure 12. Turn-Off Characteristics vs. Collector Current



Typical Performance Characteristics (Continued)

Figure 13. Switching Loss vs. Collector Current

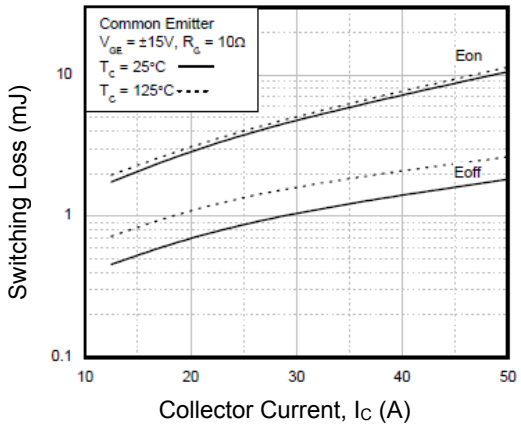


Figure14. Gate Charge Characteristics

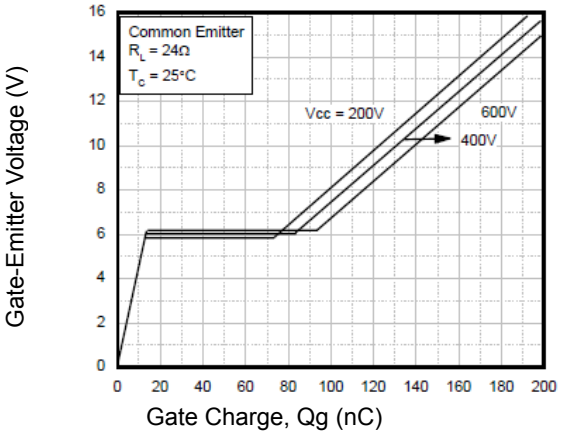


Figure 15. SOA Characteristics

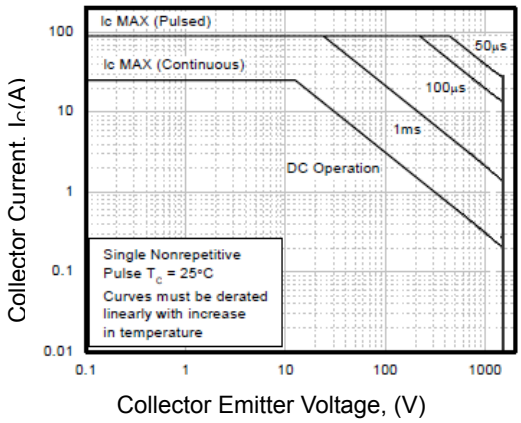


Figure 16. Turn-Off SOA

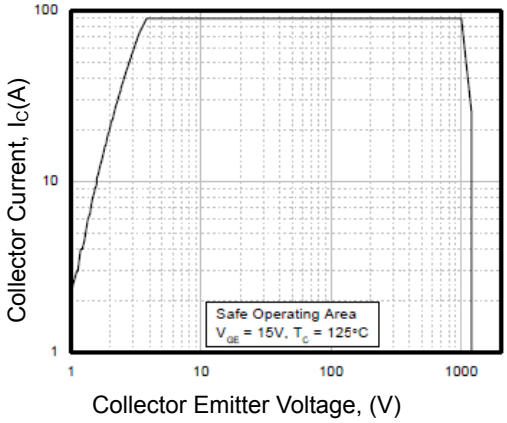
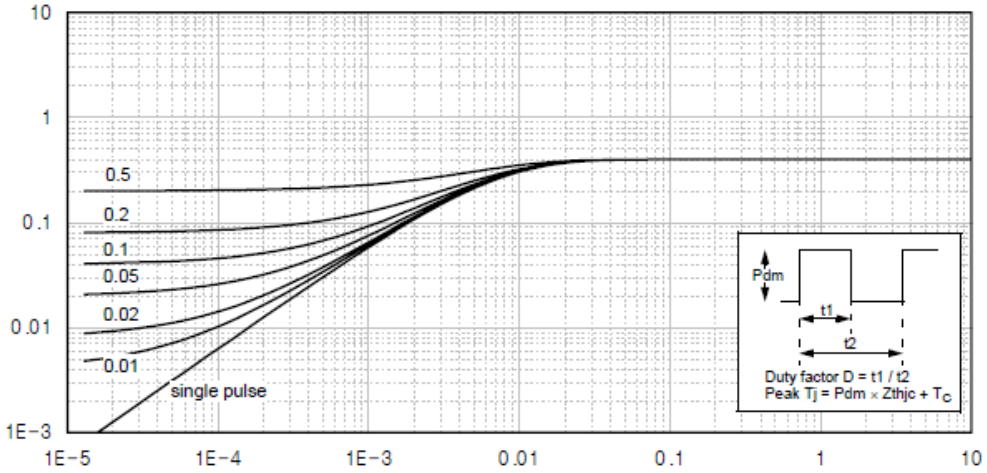
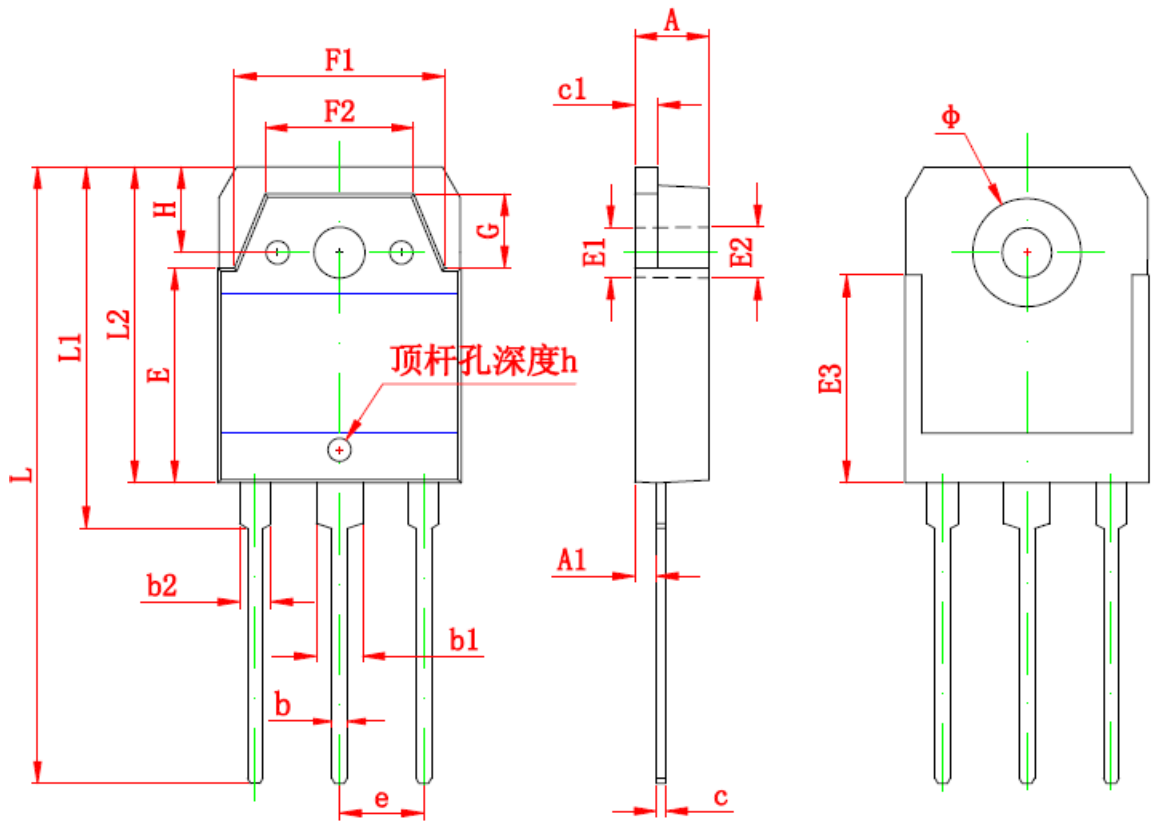


Figure 17. Transient Thermal Impedance of IGBT



TO-3P Mechanical Dimensions (continued)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.600	5.000	0.181	0.197
A1	1.200	1.600	0.047	0.063
b	0.800	1.200	0.031	0.047
b1	2.800	3.200	0.110	0.126
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
c1	1.450	1.650	0.057	0.065
D	15.450	15.850	0.606	0.622
E	13.700	14.100	0.539	0.555
E1	3.200 REF		0.126 REF	
E2	3.300 REF		0.130 REF	
E3	13.450 REF		0.530 REF	
F1	13.400	13.800	0.528	0.543
F2	9.400	9.800	0.370	0.386
L	39.900	40.300	1.571	1.587
L1	23.200	23.600	0.913	0.929
L2	20.300	20.600	0.799	0.811
Φ	6.900	7.100	0.272	0.280
G	5.150	5.550	0.203	0.219
e	5.450 TYP		0.215 TYP	
H	5.000 REF		0.197 REF	
h	0.000	0.300	0.000	0.012

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